

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI 2223-20** is a Common Base Device Designed for high gain & efficiency telemetry applications.

FEATURES:

- Internal Input/Output Matching Networks
- Emitter Balasting
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	600 mA
V_{CC}	28 V
P_{DISS}	55 W @ T _C ≤ 50 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	2.7 °C/W

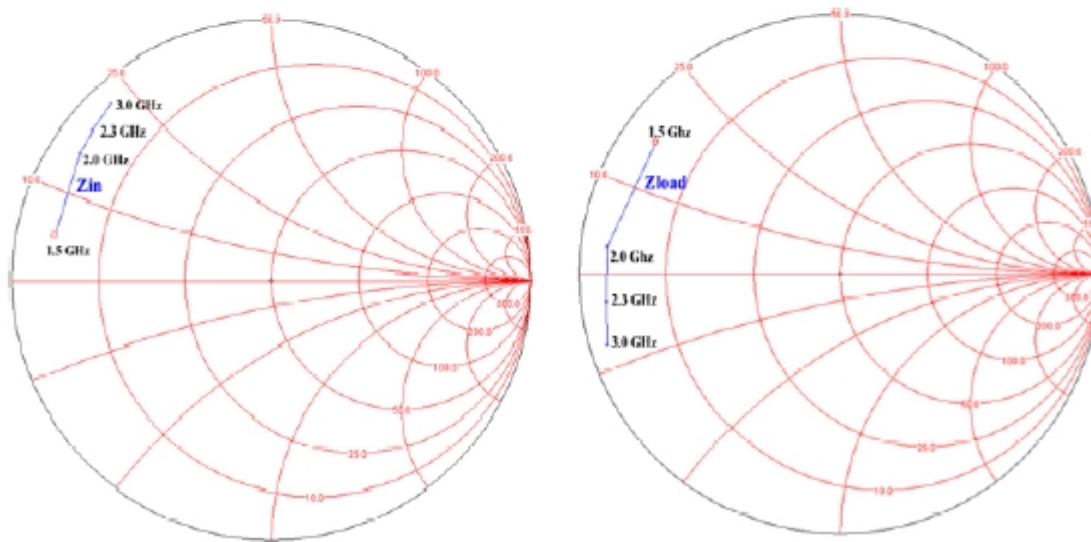
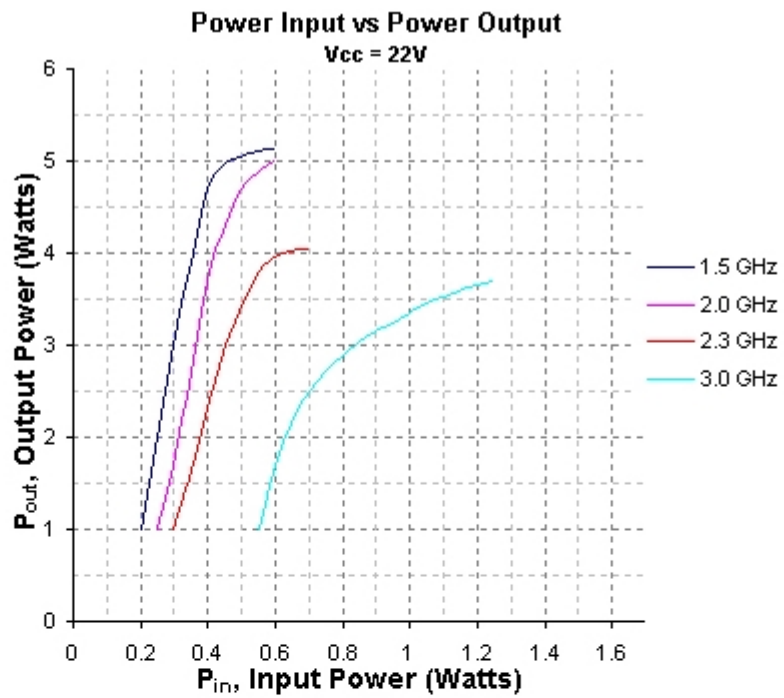
PACKAGE STYLE .310 2L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	.100 / 2.54	.120 / 3.05
C	.050 / 1.27	
D	.286 / 7.26	.306 / 7.77
E	.110 / 2.79	.130 / 3.30
F	.306 / 7.77	.318 / 8.08
G		.148 / 3.76
H		.400 / 10.16
I		.119 / 3.02
J	.552 / 14.02	.572 / 14.53
K	.790 / 20.07	.810 / 20.57
L	.300 / 7.62	.320 / 8.13
M	.003 / 0.08	.006 / 0.15
N	.052 / 1.32	.072 / 1.83
P	.118 / 3.00	.131 / 3.33
R		.230 / 5.84

ORDER CODE: ASI10533

CHARACTERISTICS T_C = 25 °C

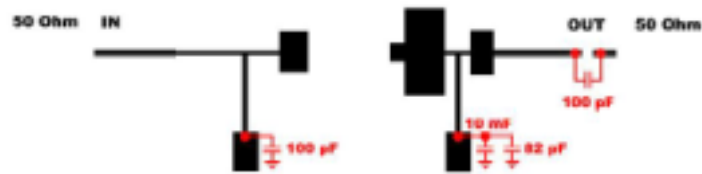
SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 12 mA	40			V
BV_{CER}	I _C = 25 mA R _{BE} = 10 Ω	28			V
BV_{EBO}	I _E = 2.5 mA	3.0			V
h_{FE}	V _{CE} = 8.0 V I _C = 100 mA	20	60	100	---
C_{CB}	I _E = 0 V f = 1.0 MHz	1.3	2.0		pF
P_G	V _{CC} = 24 V P _{OUT} = 20 W f = 2.2 – 2.3 GHz	7.0			dB
η_c	I _C = 200 mA	40			%



Test Board Template



Test Board Components



Material: 0.010" Glass Teflon DK = 2.3